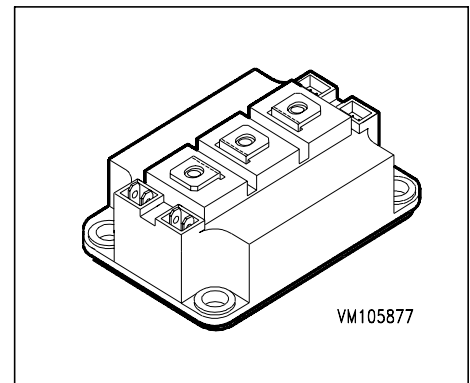


IGBT Power Module

- Single switch with chopper diode
- Package with insulated metal base plate



Type	V_{CE}	I_C	Package	Ordering Code
BSM 200 GAL 120 DN2	1200V	290A	HALFBRIDGE GAL 2B	C67070-A2301-A70

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1200	V
Collector-gate voltage	V_{CGR}	1200	V
$R_{GE} = 20 \text{ k}\Omega$		± 20	
Gate-emitter voltage	V_{GE}		
DC collector current	I_C	290	A
$T_C = 25 \text{ }^\circ\text{C}$		200	
$T_C = 80 \text{ }^\circ\text{C}$			
Pulsed collector current, $t_p = 1 \text{ ms}$	I_{Cpuls}	580	A
$T_C = 25 \text{ }^\circ\text{C}$		400	
$T_C = 80 \text{ }^\circ\text{C}$			
Power dissipation per IGBT	P_{tot}	1400	W
$T_C = 25 \text{ }^\circ\text{C}$			
Chip temperature	T_j	+ 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip case	R_{thJC}	≤ 0.09	K/W
Diode thermal resistance, chip case	R_{thJCD}	-	
Diode thermal resistance, chip-case,chopper	R_{thJCDC}	≤ 0.125	
Insulation test voltage, $t = 1 \text{ min.}$	V_{is}	2500	Vac
Creepage distance	-	20	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	-
IEC climatic category, DIN IEC 68-1	-	55 / 150 / 56	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 8\text{ mA}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_j = 125\text{ °C}$	$V_{CE(sat)}$	- -	2.5 3.1	3 3.7	
Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$	I_{CES}	- -	3 12	4 -	mA
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	400	nA

AC Characteristics

Transconductance $V_{CE} = 20\text{ V}, I_C = 200\text{ A}$	g_{fs}	108	-	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	13	-	nF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	2	-	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	1	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$ $R_{Gon} = 4.7\ \Omega$	$t_{d(on)}$	-	110	220	ns
Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$ $R_{Gon} = 4.7\ \Omega$	t_r	-	80	160	
Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 200\text{ A}$ $R_{Goff} = 4.7\ \Omega$	$t_{d(off)}$	-	550	800	
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 200\text{ A}$ $R_{Goff} = 4.7\ \Omega$	t_f	-	80	120	

Free-Wheel Diode

Diode forward voltage $I_F = 200\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 200\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_F	-	-	-	V
Reverse recovery time $I_F = 200\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2000\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$	t_{rr}	-	-	-	μs
Reverse recovery charge $I_F = 200\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2000\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rr}	-	-	-	μC

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Chopper Diode

Chopper diode forward voltage $I_{FC} = 300\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_{FC} = 300\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_{FC}	- -	2.3 1.8	2.8 -	V
Reverse recovery time, chopper $I_{FC} = 300\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2500\text{ A}/\mu\text{s}$, $T_j = 25\text{ °C}$	t_{rrC}	-	500	-	ns
Reverse recovery charge, chopper $I_{FC} = 300\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2500\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rrC}	- -	14 40	- -	μC



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